Part Number Customer

Category		**Parameter**	**Specification**	**Measurement Method**
OverallWafer	1.0	Diameter	100.00 +/- 0.20 mm	
	2.0	Primary Flat Orientation	{110}+/-1 degree	Wafer Vendor
	3.0	Primary Flat Length	32.50 +/- 2.50 mm	Wafer Vendor
	4.0	Secondary Flat Orientation	none/semi	
	5.0	Overall Thickness	602.00 +/- 15.00 µm	ADE, 100%
	6.0	Total Thickness Variation (TTV)	<5.00µm	Guaranteed by Process
	7.0	Bow	<80.00µm	ADE to ASTM F534, 20%
	8.0	Warp	<80.00µm	ADE to ASTM F657, 20%
	9.0	Edge Chips	0	Bright Light, 100% (note 2)
	10.0	Edge Exclusion	5mm	
HandleSilicon	11.0	Handle Growth Method	CZ	Wafer Vendor
	12.0	Handle Orientation	{100} +/- 1 degree	Wafer Vendor
	13.0	Handle Thickness	200.00 +/- 10.00 µm	ADE, 100%
	14.0	Handle Doping Type	Any	Wafer Vendor
	15.0	Handle Dopant	Any	Wafer Vendor
	16.0	Handle Resistivity	>0.005 Ohm cm	Wafer Vendor
	17.0	Backside Finish	Polished with lasermarking	Guaranteed by Process
BuriedOxide	18.0	Oxide Type	Thermal	
	19.0	Oxide Thickness	10,000.00 +/- 500.00 A	Nanospec centre point, 4%
	20.0	Oxide formed on	Handle Wafer	
DeviceSilicon	21.0	Device Growth Method	FZ	Wafer Vendor
	22.0	Device Orientation	{100} +/- 1 degree	Wafer Vendor
	23.0	Nominal Thickness	75.00 +/- 2.00 µm	FTIR, 100% 9-Pt (note3)
	24.0	Device Doping Type	Any	Wafer Vendor
	25.0	Device Dopant	Any	Wafer Vendor
	26.0	Device Resistivity	>2000 Ohmcm	Wafer Vendor
BuriedOxide2	27.0	Oxide 2 Type	Thermal	
	28.0	Oxide 2 Thickness	10,000.00 +/- 500.00 A	Nanospec centre point measurement, 4%
	29.0	Oxide 2 formed on	Device 2 wafer	Guaranteed by Process
DeviceSilicon2	30.0	Device 2 Growth Method	FZ	Wafer Vendor
	31.0	Device 2 Orientation	{100} +/- 1 degree	Wafer Vendor
	32.0	Device 2 Nominal Thickness	325.00 +/- 2.00 um	ADE Single point measurement (see note 3)
	33.0	Device 2 DopingType	Any	Wafer Vendor
	34.0	Device 2 Dopant	Any	Wafer Vendor
	35.0	Device 2 Resistivity	>2000 Ohmcm	Wafer Vendor

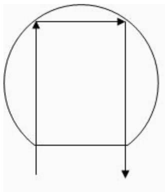
Part Number	Customer

Category		**Parameter**	**Specification**	**Measurement Method**
DeviceSilicon	36.0	Voids	none	Wafer Vendor
	37.0	Scratches	0	Bright Light, 100% (note 2)
	38.0	Haze	none	Bright Light, 100% (note 2)

Category	**Parameter**	**Specification**	**Measurement Method**
Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 100.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	

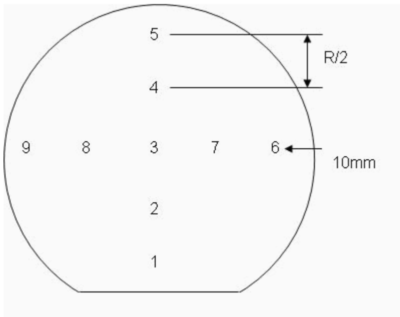
Explanatory Notes

1. Microscope inspection performed using microscope scan as below. 5x objective.



2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information